L Number	Hits	Search Text	DB	Time stamp
-	1182	(passiv$8 near (layer or region or film or medium)) and semiconductor and monolithic and integrated and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/14 09:22
-	1	((passiv$8 near (layer or region or film or medium)) and semiconductor and monolithic and integrated and substrate) and VCSEl and ((active near (layer or device or film or region or medium)) with amplif$5) and (photodiode or (photo near diode)) and (photodetect$5 or (photo near detect$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 08:59
-	3	((passiv$8 near (layer or region or film or medium)) and semiconductor and monolithic and integrated and substrate) and VCSEl and ((active near (layer or device or film or region or medium)) AND amplif$5) and (photodiode or (photo near diode)) and (photodetect$5 or (photo near detect$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 09:02
-	6	(passiv$8 near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEl and ((active near (layer or device or film or region or medium)) AND amplif$5) and (photodiode or (photo near diode)) and (photodetect$5 or (photo near detect$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 09:13
-	1	(passiv$8 near (layer or region or film or medium)) and semiconductor and 372/50 and substrate and VCSEl and ((active near (layer or device or film or region or medium)) AND amplif$5) and (photodiode or (photo near diode)) and (photodetect$5 or (photo near detect$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 09:04
-	1	(passiv$8 near (layer or region or film or medium)) and semiconductor and 372/$ and substrate and VCSEl and ((active near (layer or device or film or region or medium)) AND amplif$5) and (photodiode or (photo near diode)) and (photodetect$5 or (photo near detect$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 09:11
-	9	((passiv$8 or insulat$5) near (layer or region or film or medium)) and semiconductor and 372/$ and substrate and VCSEl and ((active near (layer or device or film or region or medium)) AND amplif$5) and (photodiode or (photo near diode)) and (photodetect$5 or (photo near detect$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 09:13
-	17	((passiv$8 or insulat$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEl and ((active near (layer or device or film or region or medium)) AND amplif$5) and (photodiode or (photo near diode)) and (photodetect$5 or (photo near detect$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 09:41
-	17	((passiv$8 or insulat$5) near (layer or region or film or medium)) and semiconductor and substrate and VCSEl and ((active near (layer or device or film or region or medium)) AND amplif$5) and (photodiode or (photo near diode)) and (photodetect$5 or (photo near detect$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 09:41

-		14	(((passiv$8 or insulat$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or region or medium)) AND amplif$5) and (photodiode or (photo near diode)) and (photodetect$5 or (photo near detect$5))) and (diode near laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 09:42
-		17	(((passiv$8 or insulat$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or region or medium)) AND amplif$5) and (photodiode or (photo near diode)) and (photodetect$5 or (photo near detect$5))) and diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:17
-		11	((((passiv$8 or insulat$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or region or medium)) AND amplif$5) and (photodiode or (photo near diode)) and (photodetect$5 or (photo near detect$5))) and diode) and (contact near (layer or device or region or film or medium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:22
-		6	((((passiv$8 or insulat$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or region or medium)) AND amplif$5) and (photodiode or (photo near diode)) and (photodetect$5 or (photo near detect$5))) and diode) not (((((passiv$8 or insulat$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or region or medium)) AND amplif$5) and (photodiode or (photo near diode)) and (photodetect$5 or (photo near detect$5))) and diode) and (contact near (layer or device or region or film or medium)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:27
-		2	mesa and (((((passiv$8 or insulat$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or region or medium)) AND amplif$5) and (photodiode or (photo near diode)) and (photodetect$5 or (photo near detect$5))) and diode) and (contact near (layer or device or region or film or medium)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:27
-		11	amplif$5 and (((((passiv$8 or insulat$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or region or medium)) AND amplif$5) and (photodiode or (photo near diode)) and (photodetect$5 or (photo near detect$5))) and diode) and (contact near (layer or device or region or film or medium)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:27

-	0	(((((passiv$8 or insulat$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or region or medium)) AND amplif$5) and (photodiode or (photo near diode)) and (photodetect$5 or (photo near detect$5))) and diode) and (contact near (layer or device or region or film or medium))) not (amplif$5 and (((((passiv$8 or insulat$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or region or medium)) AND amplif$5) and (photodiode or (photo near diode)) and (photodetect$5 or (photo near detect$5))) and diode) and (contact near (layer or device or region or film or medium))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:28
-	11	(((((passiv$8 or insulat$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or region or medium)) AND amplif$5) and (photodiode or (photo near diode)) and (photodetect$5 or (photo near detect$5))) and diode) and (contact near (layer or device or region or film or medium))) AND t (amplif$5 and (((((passiv$8 or insulat$5) near (layer or region or film or medium)) and semiconductor and integrated and substrate and VCSEI and ((active near (layer or device or film or region or medium)) AND amplif$5) and (photodiode or (photo near diode)) and (photodetect$5 or (photo near detect$5))) and diode) and (contact near (layer or device or region or film or medium))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:28
-	24698	(substrate near3 (GaAs or AsGa))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/25 12:01
-	1390	(substrate near3 (GaN or NGa))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 11:28
-	17941	(substrate near3 (InP or PIn))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 11:28
-	78	((substrate near3 (GaAs or AsGa))) and ((substrate near3 (GaN or NGa))) and ((substrate near3 (InP or PIn)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 11:29
-	0	"11" and photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 11:29

-	0	("11" and photodiode) and (photodiode or photodetect$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 11:30
-	11	(((substrate near3 (GaAs or AsGa))) and ((substrate near3 (GaN or NGa))) and ((substrate near3 (InP or PIn)))) and VCSEl	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 11:30
-	543	((passiv$8 near (layer or region or film or medium)) with (window or aperture)) and (semiconductor or VCSEL) and substrate and active	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/14 13:41
-	6	((passiv$8 near (layer or region or film or medium)) with (window or aperture)) and (VCSEL) and substrate and active	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/07/14 13:43